

December 2014

FDZ193P

P-Channel 1.7V PowerTrench[®] WL-CSP MOSFET $_{-20V, -1A, 90m\Omega}$

Features

- Max $r_{DS(on)}$ = 90m Ω at V_{GS} = -4.5V, I_D = -1A
- Max $r_{DS(on)}$ = 130m Ω at V_{GS} = -2.5V, I_D = -1A
- Max $r_{DS(on)}$ = 300m Ω at V_{GS} = -1.7V, I_D = -1A
- Occupies only 1.5 mm² of PCB area Less than 50% of the area of 2 x 2 BGA
- Ultra-thin package: less than 0.65 mm height when mounted to PCB
- RoHS Compliant

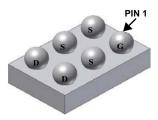


General Description

Designed on Fairchild's advanced 1.7V PowerTrench® process with state of the art "low pitch" WLCSP packaging process, the FDZ193P minimizes both PCB space and $r_{DS(on)}$. This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low $r_{DS(on)}$.

Application

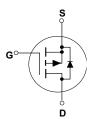
- Battery management
- Load switch
- Battery protection











MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DS}	Drain to Source Voltage		-20	V
V _{GS}	Gate to Source Voltage		±12	V
I _D	Drain Current -Continuous	(Note 1a)	-3	^
	-Pulsed		-15	A
Б	Power Dissipation	(Note 1a)	1.9	10/
P_D	Power Dissipation	(Note 1b)	0.9	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	65	• C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	133	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
2	FDZ193P	WL-CSP	7"	8mm	5000 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		-11		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16V, V _{GS} = 0V			-1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12V, V_{GS} = 0V$			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.6	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		3		mV/°C
		$V_{GS} = -4.5V, I_{D} = -1A$		66	90	
 -	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -1A$		92	130	mΩ
DS(on)		$V_{GS} = -1.7V, I_D = -1A$		195	300	11152
		$V_{GS} = -4.5V$, $I_D = -1A T_J = 125$ °C		84	123	
I _{D(on)}	On to State Drain Current	$V_{GS} = -4.5V, V_{DS} = -5V$	-10			Α
9 _{FS}	Forward Transconductance	$V_{DS} = -5V, I_{D} = -1A$		5.6		S

Dynamic Characteristics

C _{iss}	Input Capacitance	\\ - 10\\ \\ - 0\\	660	pF
C _{oss}	Output Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz	150	pF
C _{rss}	Reverse Transfer Capacitance	1 - 111112	90	pF
R_q	Gate Resistance	f = 1MHz	9.5	Ω

Switching Characteristics

	<u> </u>		 		
t _{d(on)}	Turn-On Delay Time	10/1	13	23	ns
t _r	Rise Time	$V_{DD} = -10V, I_{D} = -1A$ $V_{GS} = -4.5V, R_{GEN} = 6\Omega$	10	20	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = -4.3V, N _{GEN} = 052	28	45	ns
t _f	Fall Time		21	34	ns
Q _{g(TOT)}	Total Gate Charge at 10V	$V_{GS} = 0V \text{ to } 10V V_{DD} = -10V$	7	10	nC
Q _{gs}	Gate to Source Gate Charge	I _D = -1A	1		nC
Q _{ad}	Gate to Drain "Miller" Charge		2		nC

Drain-Source Diode Characteristics

I _S	Maximum continuous Drain-Source Diode Forward Current			-1.1	Α
V_{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0V, I _S = -1.1A (Note 2)	-0.7	-1.2	V
t _{rr}	Reverse Recovery Time	I _F = -1A, di/dt = 100A/μs	19		ns
Q _{rr}	Reverse Recovery Charge	1F 1A, αι/αι - 100A/μS	6		nC

Notes:

1: R_{0,0,A} is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. The thermal resistance from the junction to the circuit board side of the solder ball, R_{0,0,B} is defined for reference. For R_{0,0,C} the thermal reference point for the case is defined as the top surface of the copper chip carrier. R_{0,0,C} and R_{0,0,B} are guaranteed by design while R_{0,0,A} is determined by the user's board design.



a. 65°C/W when mounted on a 1 in² pad of 2 oz copper,1.5" X 1.5" X 0.062" thick PCB



b. 133°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < $300\mu s$, Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

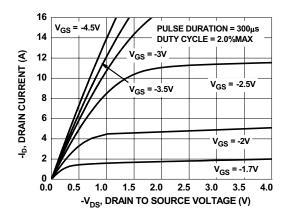


Figure 1. On Region Characteristics

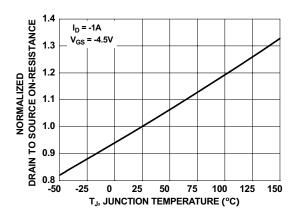


Figure 3. Normalized On Resistance vs Junction Temperature

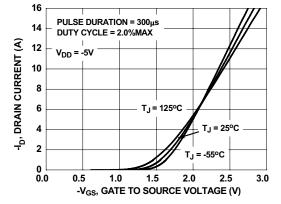


Figure 5. Transfer Characteristics

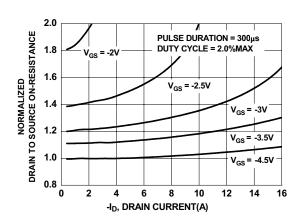


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

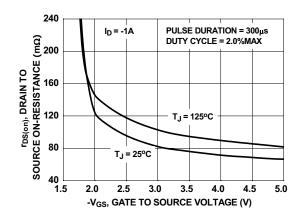


Figure 4. On-Resistance vs Gate to Source Voltage

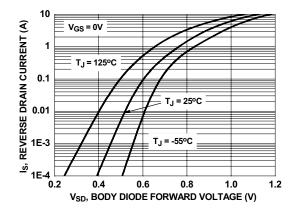


Figure 6. Source to Drain Diode Forward Voltage vs Source Current



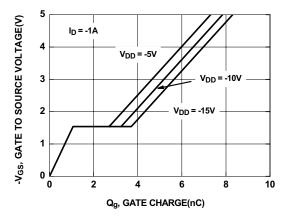


Figure 7. Gate Charge Characteristics

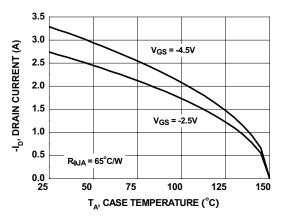


Figure 9. Maximum Continuous Drain Current vs Ambient Temperature

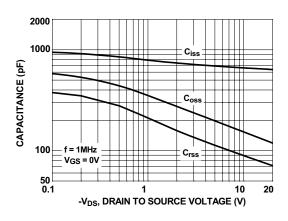


Figure 8. Capacitance vs Drain to Source Voltage

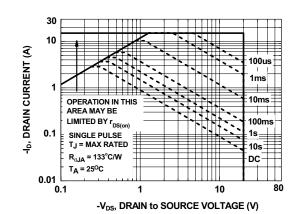


Figure 10. Forward Bias Safe Operating Area

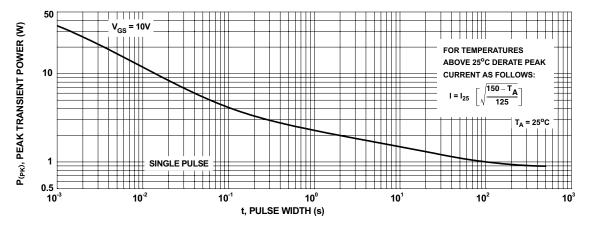


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

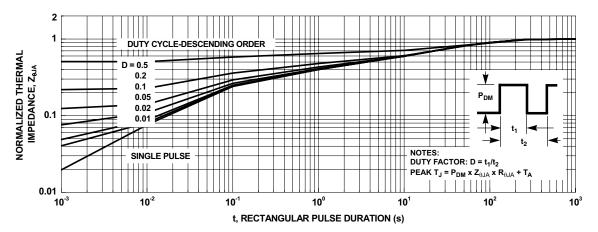
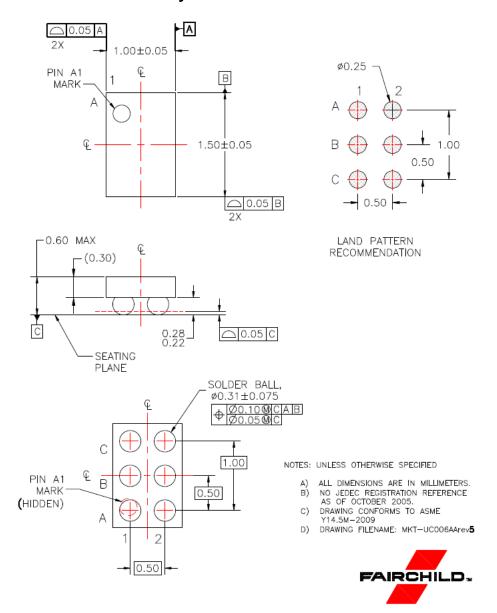


Figure 12. Transient Thermal Response Curve

Dimensional Outline and Pad Layout



Pin Definations:

Gate	Drain	Source
A1	C1, C2	A2, B1, B2

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings: http://www.fairchildsemi.com/package/packageDetails.html?id=PN_UCBAU-006





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

F-PFS™ AttitudeEngine™ FRFET®

Global Power Resource SM Awinda® AX-CAP®* GreenBridge™ BitSiC™ Green FPS™

Build it Now™ Green FPS™ e-Series™

CorePLUS™ Gmax™ CorePOWER™ GTO™ CROSSVOLT™ IntelliMAX™ CTL™ ISOPLANAR™

Current Transfer Logic™ Making Small Speakers Sound Louder

MegaBuck[™]

MicroFET™

MicroPak™

MicroPak2™

MillerDrive™

MotionMax™

MotionGrid®

mWSaver®

OptoHiT™

OPTOLOGIC®

MTi®

 $\mathsf{MTx}^{^{\circledR}}$

MVN[®]

and Better™

MIČROCOUPLER™

DEUXPEED Dual Cool™ EcoSPARK®

EfficientMax™ **ESBC™**

Fairchild Fairchild Semiconductor® FACT Quiet Series™ FACT FAST®

FastvCore[™] FETBench™ OPTOPLANAR®

PowerTrench® PowerXS™

Programmable Active Droop™

QFĔT QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM® STEALTH™ SuperFET SuperSOT™3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™ Sync-Lock™

TinyBoost[®] TinyBuck TinyCalc™ TinyLogic[®] TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®*

SYSTEM GENERAL®

UHC Ultra FRFET™ UniFET™ VCXTN VisualMax™

uSerDes™

VoltagePlus™ XS™ Xsens™ 仙童™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. T

FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN: NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS. NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FARCHILD SEMICONDUCTOR CORPORATION.

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com,

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 173

^{*} Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

FDZ193P